IN THE CLAIMS

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Currently Amended) An encapsulation structure for a display device, comprising:

a dielectric sealing structure that seals protruding structures, the dielectric sealing structure being non-planar and conforming to a shape of the protruding structures; and

stabilization layer located over the dielectric sealing structure to form a substantially planar surface;

wherein the protruding structures have negative slopes that form shadow regions.

2. (Previously Presented) The encapsulation structure according to claim 1, wherein said stabilization layer is of a

polymeric material.

3.(Previously Presented) he encapsulation structure according to claim 1, wherein said sealing structure comprises a first layer of a first dielectric material and a second layer of a second dielectric material.

4.(Previously Presented) The encapsulation structure according to claim 3, wherein said sealing structure further comprises a third layer of a third dielectric material.

5.(Previously Presented) The encapsulation structure according to claim 4, wherein said third dielectric material is the same as said first dielectric material.

6.(Previously Presented) The encapsulation structure according to claim 3, wherein said first dielectric material is selected from the group comprising silicon nitride, aluminium nitride and any mixture thereof, and wherein said second dielectric

material is selected from the group comprising silicon oxide, silicon oxide fluoride, titanium oxide, tantalum oxide, zirconium oxide, hafnium oxide, aluminium oxide and any mixture thereof.

7.(Previously Presented) The encapsulation structure according to claim 3, wherein said first dielectric material is selected from the group comprising silicon oxide, silicon oxide fluoride, titanium oxide, tantalum oxide, zirconium oxide, hafnium oxide, aluminium oxide and any mixture thereof, and wherein said second dielectric material is selected from the group comprising silicon nitride, aluminium nitride and any mixture thereof.

Claim 8 (Canceled)

9.(Previously Presented) The encapsulation structure according to claim 1, wherein an essentially cavity-free interface is formed between said stabilization layer and said sealing structure.

10. (Previously Presented) The encapsulation structure according to claim 1, wherein the thermal expansion coefficient of said stabilization layer is essentially the same as the thermal expansion coefficient of said sealing structure.

11. (Previously Presented) The encapsulation structure according to claim 1, wherein the thickness of said stabilization layer is at least 0.1 μm.

12. (Previously Presented) The encapsulation structure according to claim 1, wherein said encapsulation structure is transparent.

13. (Previously Presented) The encapsulation structure according to claim 1, wherein said stabilization layer is of a non-polymeric material.

14. (Previously Presented) The encapsulation structure according to claim 13, wherein said non-polymeric material is a

cured inorganic material.

Claims 15-19 (Canceled)

20. (Previously Presented) The encapsulation structure according to claim 1, wherein said display device is selected from a polyLED display, an OLED display or a Liquid Crystal Display.

Claim 21 (Canceled)

22. (Currently Amended) A method for manufacturing an encapsulation structure for a display device comprising the acts of:

depositing a dielectric sealing structure that seals protruding structures, the dielectric sealing structure being non-planar and conforming to a shape of the protruding structures; and

depositing a stabilization layer over the dielectric sealing structure to form a planar surface;

wherein the protruding structures have negative slopes that

form shadow regions.

23. (Previously Presented) The method according to claim 22, wherein said depositing of the stabilization layer comprises depositing a curable composition, and curing said curable composition.

24. (Previously Presented) The method according to claim 23, wherein said curing is thermal curing.

25. (Previously Presented) The method according to claim 22 wherein said stabilization layer is deposited by inkjet printing.

26. (Previously Presented) The method according to claim 22 wherein said display device is selected from a polyLED display, an OLED display and a LCD display.

27. (Previously Presented) A display device comprising an encapsulation structure according to claim 1.

28. (Previously Presented) A display device obtainable by the method according to claim 22.

29. (Previously Presented) The encapsulation structure of claim 1, wherein the dielectric sealing structure comprises silicon oxide fluoride.

30. (Previously Presented) The encapsulation structure of claim 1, wherein the stabilization layer comprises Indium.

31. (Previously Presented) The method of claim 22, further comprising the act of selecting materials for the dielectric sealing structure and stabilization layer such that the materials have substantially equal thermal expansion coefficients.

32. (Previously Presented) The method of claim 22, wherein the depositing the dielectric sealing structure is performed at 80°C.